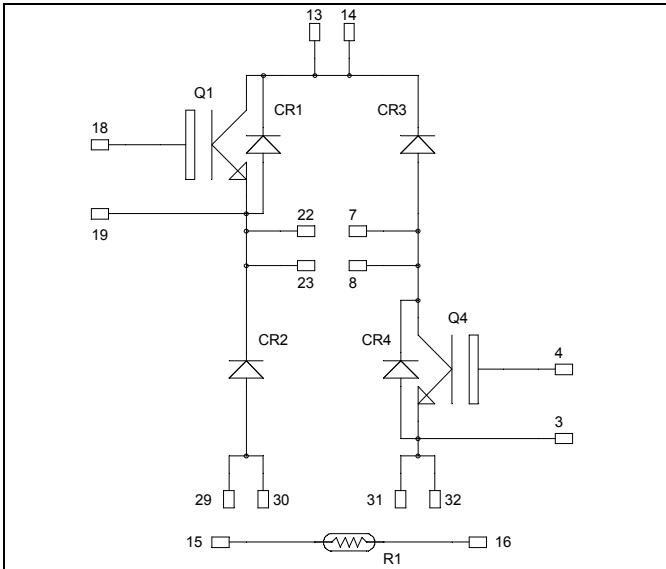


Asymmetrical - Bridge NPT IGBT Power Module

$V_{CES} = 600V$
 $I_C = 90A @ T_c = 80^\circ C$

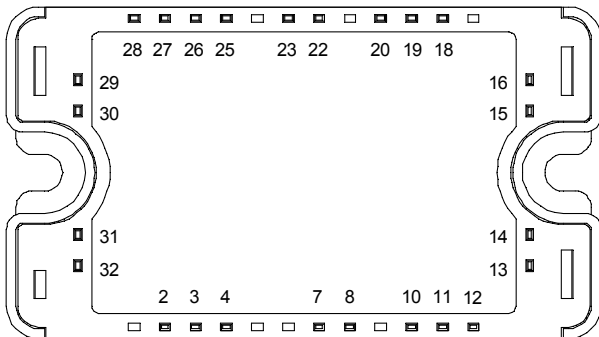


Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- RoHS compliant

All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Absolute maximum ratings

| Symbol | Parameter | Max ratings | Unit |
|-----------|---------------------------------------|---------------------|-------------|
| V_{CES} | Collector - Emitter Breakdown Voltage | 600 | V |
| I_C | Continuous Collector Current | $T_c = 25^\circ C$ | 110 |
| | | $T_c = 80^\circ C$ | 90 |
| I_{CM} | Pulsed Collector Current | $T_c = 25^\circ C$ | 200 |
| V_{GE} | Gate - Emitter Voltage | ± 20 | V |
| P_D | Maximum Power Dissipation | $T_c = 25^\circ C$ | 416 |
| RBSOA | Reverse Bias Safe Operating Area | $T_j = 150^\circ C$ | 200A @ 600V |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|---------------|--------------------------------------|--------------------------------|---------------------------|-----|-----|---------------|
| I_{CES} | Zero Gate Voltage Collector Current | $V_{GE} = 0V, V_{CE} = 600V$ | | | 250 | μA |
| $V_{CE(sat)}$ | Collector Emitter Saturation Voltage | $V_{GE} = 15V$ $I_C = 100A$ | $T_j = 25^\circ\text{C}$ | 2 | 2.5 | V |
| | | | $T_j = 125^\circ\text{C}$ | | 2.2 | |
| $V_{GE(th)}$ | Gate Threshold Voltage | $V_{GE} = V_{CE}, I_C = 1.5mA$ | 4.5 | 5.5 | 6.5 | V |
| I_{GES} | Gate – Emitter Leakage Current | $V_{GE} = 20V, V_{CE} = 0V$ | | | 400 | nA |

Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|--------------|------------------------------|--|---------------------------|-----|-----|------|
| C_{ies} | Input Capacitance | $V_{GE} = 0V ; V_{CE} = 25V$ $f = 1MHz$ | | 4.3 | | nF |
| C_{res} | Reverse Transfer Capacitance | | | 0.4 | | |
| Q_G | Gate charge | $V_{GE} = 15V ; V_{CE} = 300V$ $I_C = 100A$ | | 240 | | nC |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 100A$ $R_G = 2.2\Omega$ | | 25 | | ns |
| T_r | Rise Time | | | 10 | | |
| $T_{d(off)}$ | Turn-off Delay Time | | | 130 | | |
| T_f | Fall Time | | | 20 | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 100A$ $R_G = 2.2\Omega$ | | 25 | | ns |
| T_r | Rise Time | | | 11 | | |
| $T_{d(off)}$ | Turn-off Delay Time | | | 150 | | |
| T_f | Fall Time | | | 30 | | |
| E_{on} | Turn-on Switching Energy | $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 100A$ $R_G = 2.2\Omega$ | $T_j = 125^\circ\text{C}$ | 1 | | mJ |
| E_{off} | Turn-off Switching Energy | | $T_j = 125^\circ\text{C}$ | 3 | | |
| I_{sc} | Short Circuit data | $V_{GE} \leq 15V ; V_{Bus} = 360V$ $t_p \leq 10\mu\text{s} ; T_j = 125^\circ\text{C}$ | | 450 | | A |

Diode ratings and characteristics (CR2 & CR3)

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|-----------|---|------------------------------|---------------------------|------|-----|---------------|
| V_{RRM} | Maximum Peak Repetitive Reverse Voltage | | 600 | | | V |
| I_{RM} | Maximum Reverse Leakage Current | $V_R = 600V$ | $T_j = 25^\circ\text{C}$ | | 100 | μA |
| | | | $T_j = 125^\circ\text{C}$ | | 500 | |
| I_F | DC Forward Current | $T_c = 80^\circ\text{C}$ | | 100 | | A |
| V_F | Diode Forward Voltage | $I_F = 100A$ | | 1.6 | 2 | V |
| | | $I_F = 200A$ | | 2 | | |
| | | $I_F = 100A$ | $T_j = 125^\circ\text{C}$ | 1.3 | | |
| t_{rr} | Reverse Recovery Time | $I_F = 100A$ $V_R = 400V$ | $T_j = 25^\circ\text{C}$ | 160 | | ns |
| | | | $T_j = 125^\circ\text{C}$ | 220 | | |
| Q_{rr} | Reverse Recovery Charge | $di/dt = 200A/\mu\text{s}$ | $T_j = 25^\circ\text{C}$ | 290 | | nC |
| | | | $T_j = 125^\circ\text{C}$ | 1530 | | |

CR1 & CR4 are IGBT protection diodes only

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol | Characteristic | Min | Typ | Max | Unit |
|-----------------------------------|----------------------------|-----|------|-----|------|
| R ₂₅ | Resistance @ 25°C | | 50 | | kΩ |
| ΔR ₂₅ /R ₂₅ | | | 5 | | % |
| B _{25/85} | T ₂₅ = 298.15 K | | 3952 | | K |
| ΔB/B | T _C = 100°C | | 4 | | % |

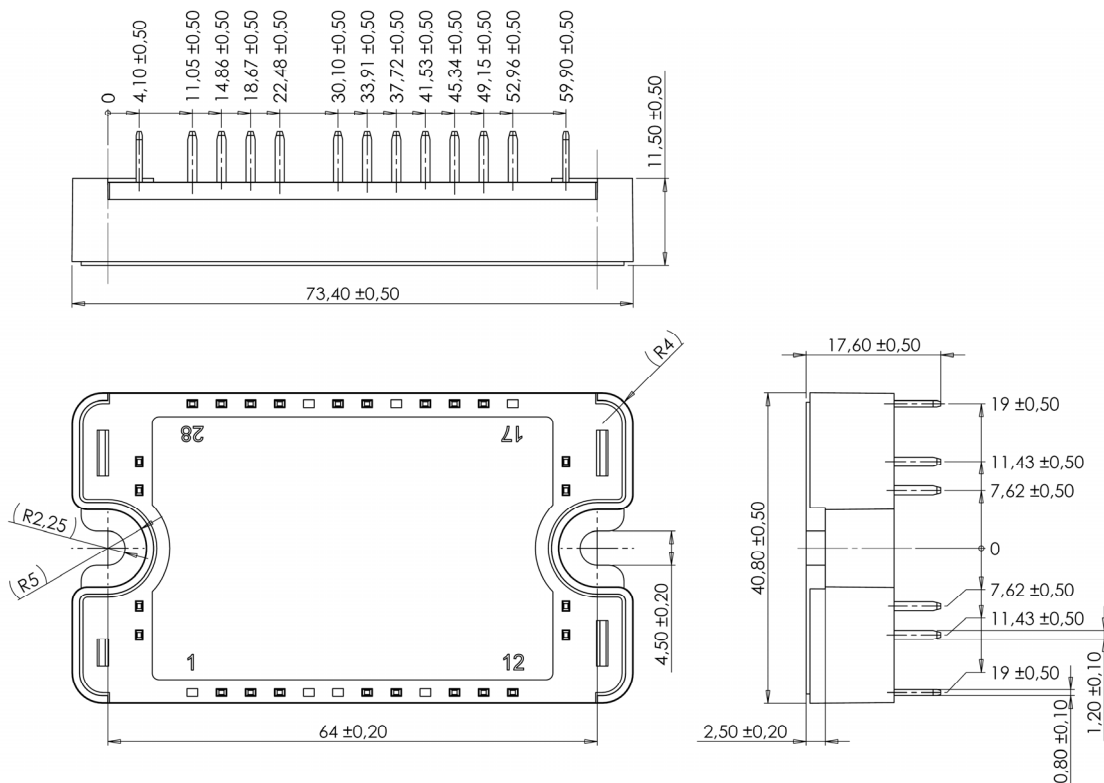
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

Thermal and package characteristics

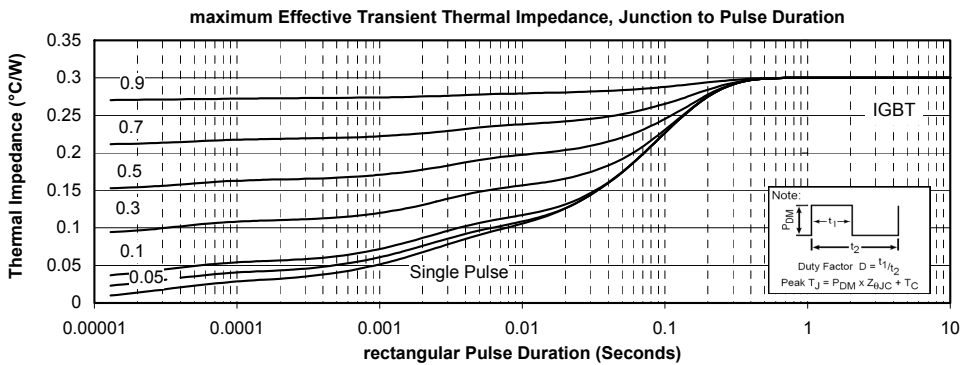
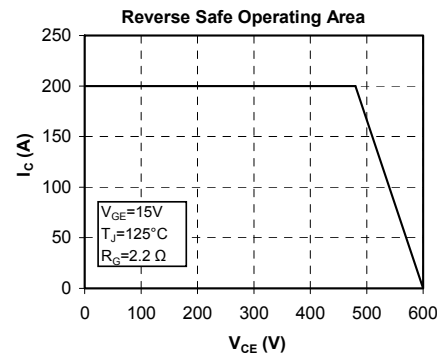
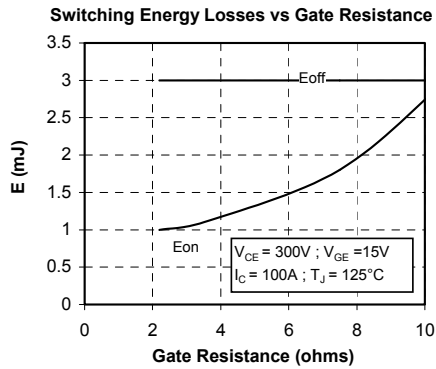
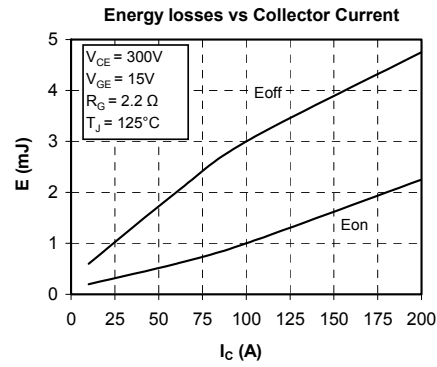
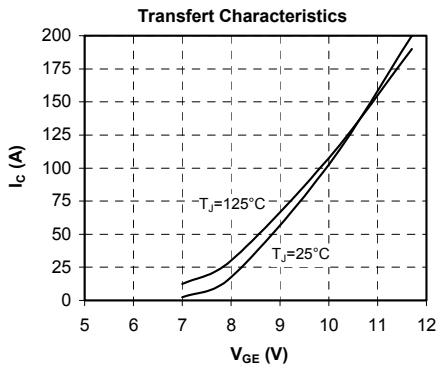
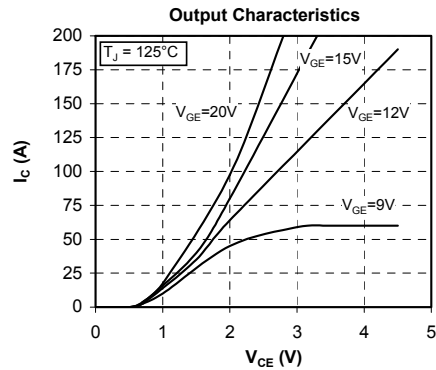
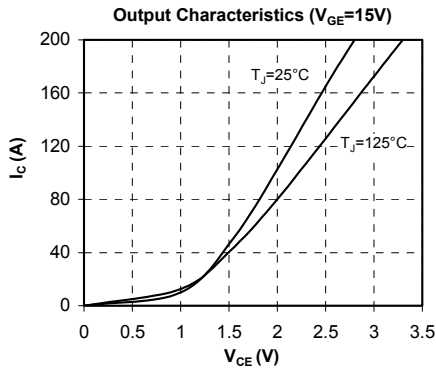
| Symbol | Characteristic | Min | Typ | Max | Unit | |
|-------------------|--|-------------|-----|------|------|-----|
| R _{thJC} | Junction to Case Thermal Resistance | IGBT | | 0.3 | °C/W | |
| | | Diode | | 0.55 | | |
| V _{ISOL} | RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz | 4000 | | | V | |
| T _J | Operating junction temperature range | -40 | | 150 | °C | |
| T _{STG} | Storage Temperature Range | -40 | | 125 | | |
| T _C | Operating Case Temperature | -40 | | 100 | | |
| Torque | Mounting torque | To heatsink | M4 | 2 | 3 | N.m |
| Wt | Package Weight | | | | 110 | g |

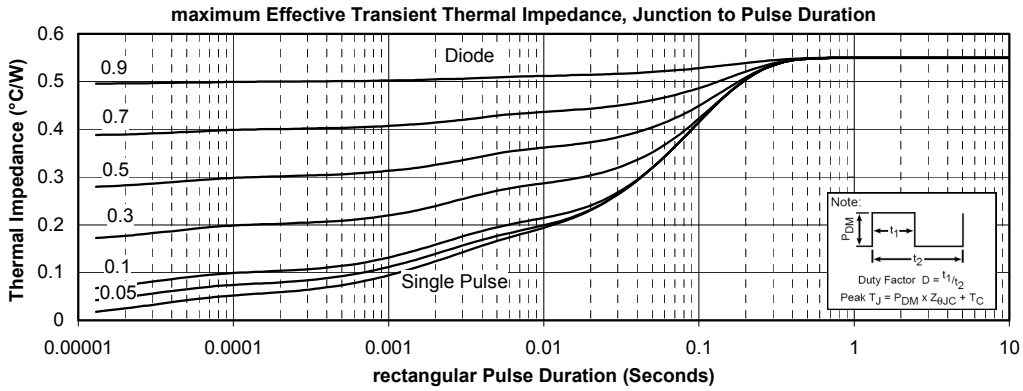
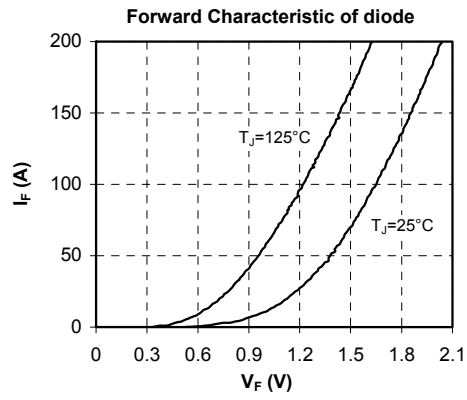
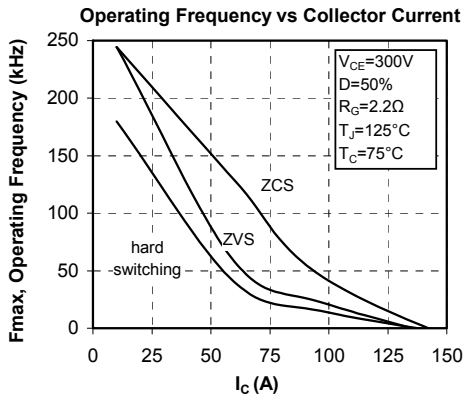
SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve





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